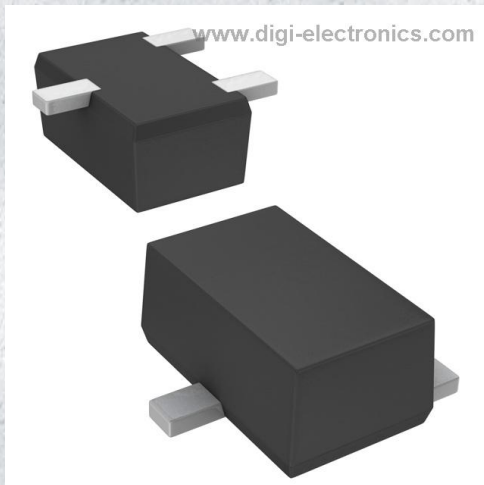


MTM231230L Datasheet



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	MTM231230L-DG
Manufacturer	Panasonic Electronic Components
Manufacturer Product Number	MTM231230L
Description	MOSFET P-CH 20V 3A SMini3-G1
Detailed Description	P-Channel 20 V 3A (Ta) 500mW (Ta) Surface Mount SMini3-G1



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RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

MTM231230L

Series:

-

FET Type:

P-Channel

Drain to Source Voltage (Vdss):

20 V

Drive Voltage (Max Rds On, Min Rds On):

2.5V, 4.5V

Vgs(th) (Max) @ Id:

1.3V @ 1mA

Input Capacitance (Ciss) (Max) @ Vds:

1000 pF @ 10 V

Power Dissipation (Max):

500mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

SC-70, SOT-323

Manufacturer:

Panasonic Electronic Components

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

3A (Ta)

Rds On (Max) @ Id, Vgs:

55mOhm @ 1A, 4V

Vgs (Max):

±10V

FET Feature:

-

Operating Temperature:

150°C (TJ)

Supplier Device Package:

SMini3-G1

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

HTSUS:

8541.21.0095

ECCN:

EAR99

MTM23123

Silicon P-channel MOSFET

For digital circuits

■ Features

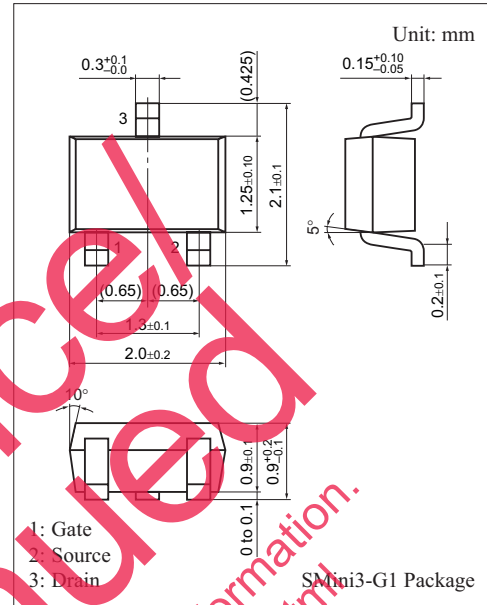
- Low voltage drive (2.5 V, 4 V)
- Realization of low on-resistance, using extremely fine process

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	-20	V
Gate-source surrender voltage	V_{GSS}	± 10	V
Drain current	I_D	-3.0	A
Peak drain current *1	I_{DP}	-16	A
Power dissipation *2	P_D	500	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

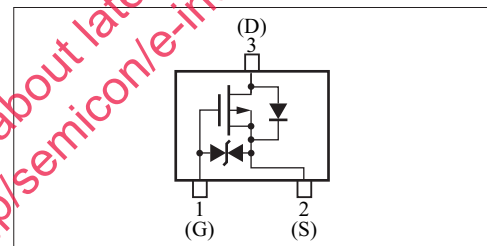
Note) *1: Pulse width $\leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

*2: Measuring on ceramic substrate at $40 \text{ mm} \times 38 \text{ mm} \times 0.1 \text{ mm}$
 Absolute maximum rating without heat sink for P_D is 150 mW



Marking Symbol: BL

Internal Connection



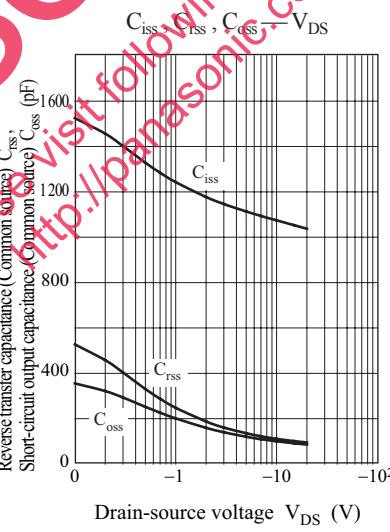
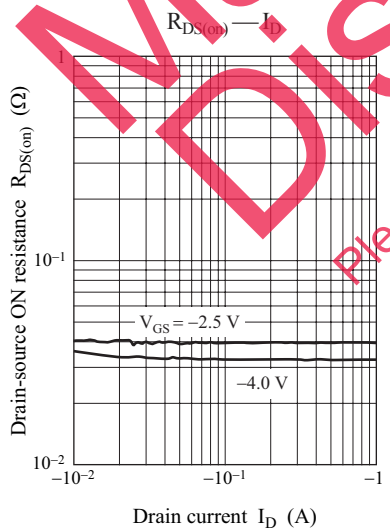
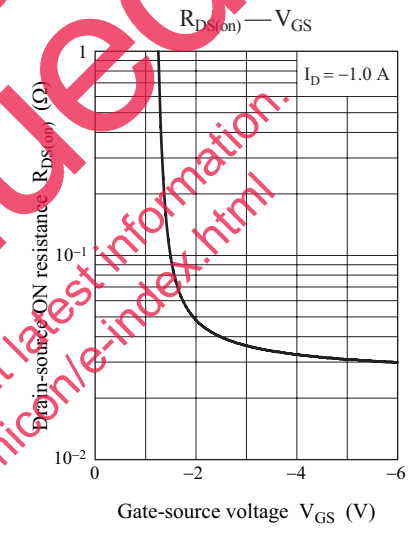
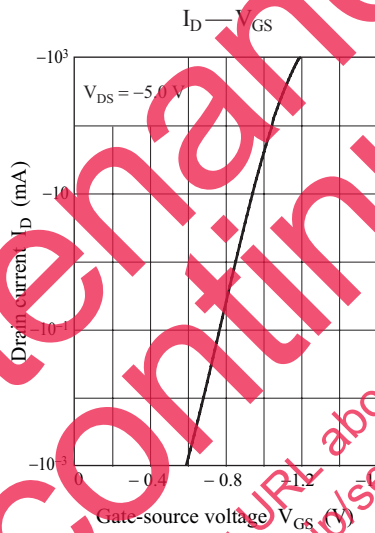
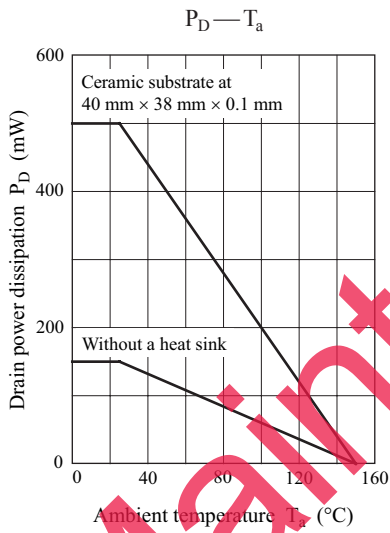
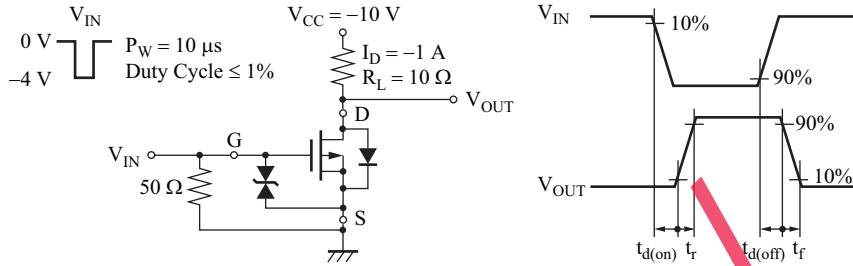
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-source surrender voltage	V_{DSS}	$I_D = -1 \text{ mA}$, $V_{GS} = 0$	-20			V	
Drain-source cutoff current	I_{DSS}	$V_{DS} = -20 \text{ V}$, $V_{GS} = 0$			-1.0	μA	
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}$, $V_{DS} = 0$			± 10	μA	
Gate threshold voltage	V_{TH}	$I_D = -1.0 \text{ mA}$, $V_{DS} = -10.0 \text{ V}$	-0.4	-0.85	-1.3	V	
Drain-source ON resistance *1	$R_{DS(on)}$	$I_D = -1 \text{ A}$, $V_{GS} = -4.0 \text{ V}$		40	55	m Ω	
		$I_D = -0.5 \text{ A}$, $V_{GS} = -2.5 \text{ V}$		45	70		
Forward transfer admittance *1	$ Y_{fs} $	$I_D = -1.0 \text{ A}$, $V_{DS} = -10 \text{ V}$, $f = 1 \text{ kHz}$	3.5			S	
Short-circuit forward transfer capacitance (Common source)	C_{iss}	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$		1000		pF	
Short-circuit output capacitance (Common source)	C_{oss}				120		pF
Reverse transfer capacitance (Common source)	C_{rss}				120		pF
Turn-on delay time *2	$t_{d(on)}$	$V_{DD} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$ to -4 V , $I_D = -1 \text{ A}$		25		ns	
Rise time *2	t_r	$V_{DD} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$ to -4 V , $I_D = -1 \text{ A}$		25		ns	
Fall time *2	t_f	$V_{DD} = -10 \text{ V}$, $V_{GS} = -4 \text{ V}$ to 0 V , $I_D = -1 \text{ A}$		70		ns	
Turn-off delay time *2	$t_{d(off)}$	$V_{DD} = -10 \text{ V}$, $V_{GS} = -4 \text{ V}$ to 0 V , $I_D = -1 \text{ A}$		120		ns	

■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement: Pulse width < 300 μs , Duty Cycle < 2.0%
- *2: Measurement circuit



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